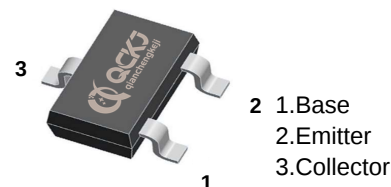


PNP Transistors

■ Features

- High Collector Current
- Complementary to SS8050W



■ Simplified outline(SOT-323)

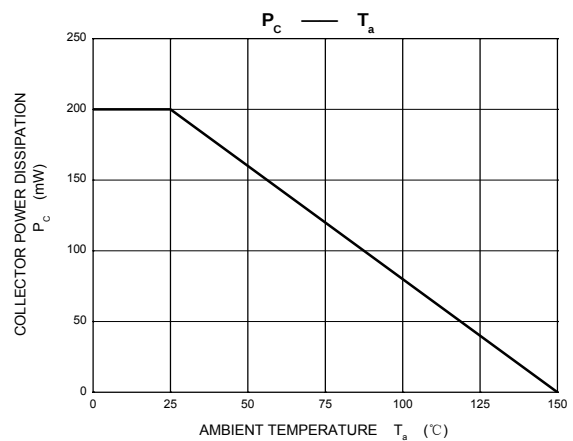
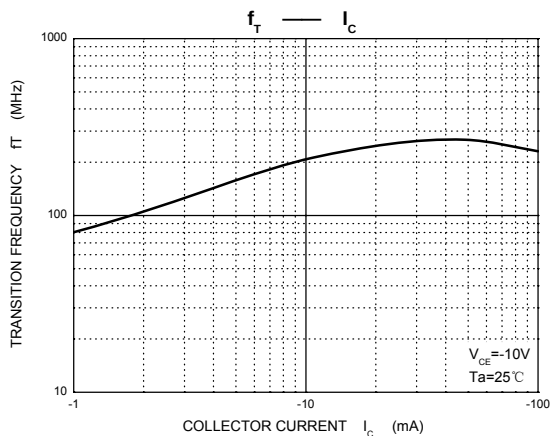
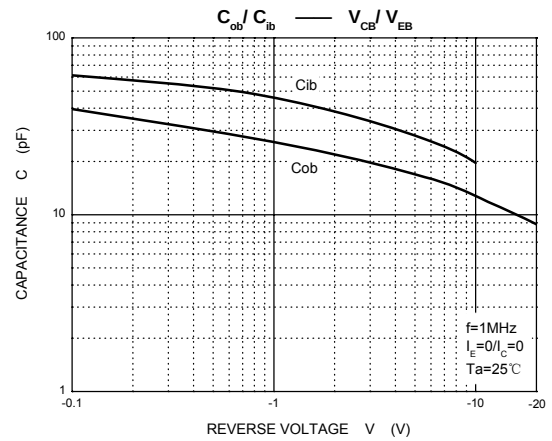
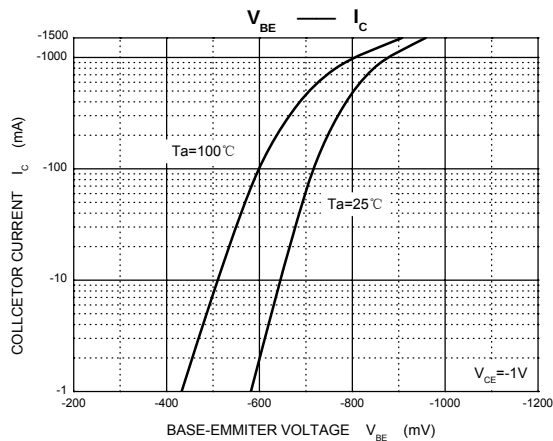
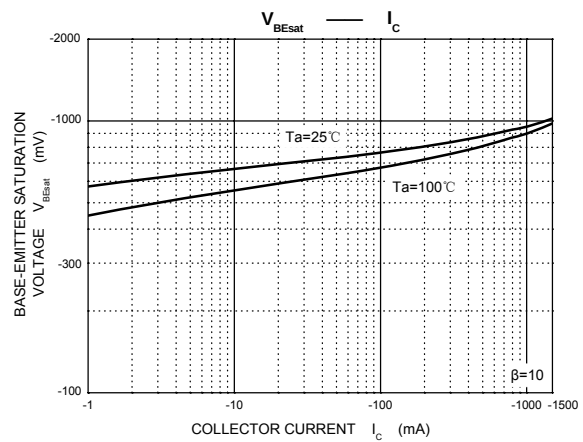
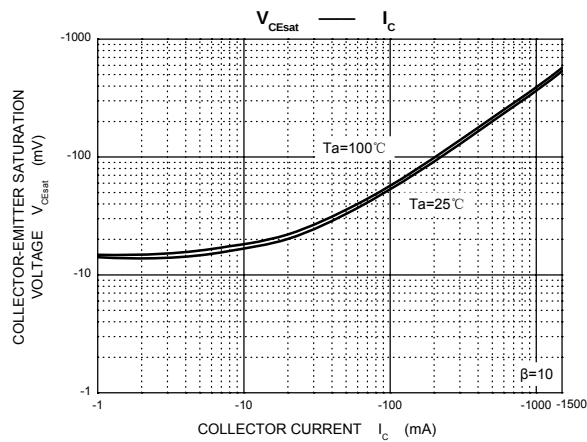
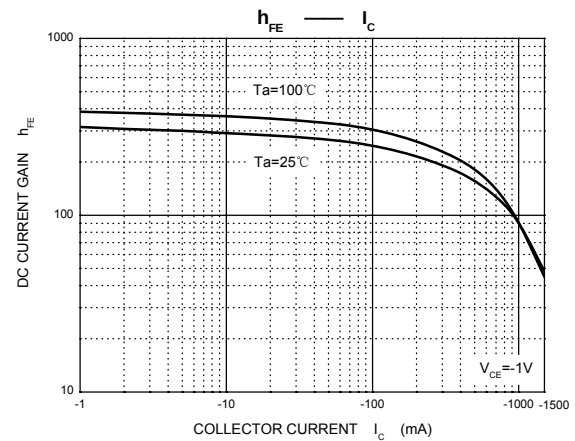
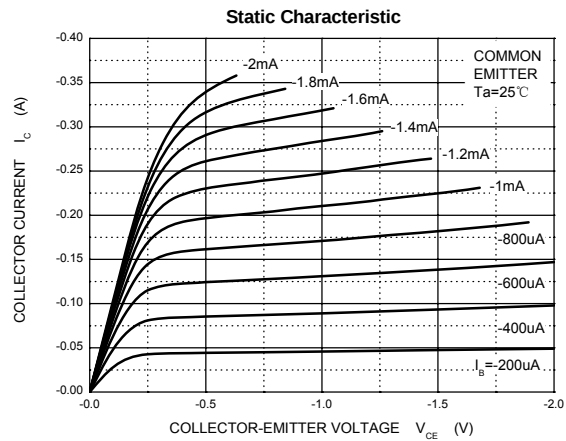
■ Absolute Maximum Ratings Ta = 25°C

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1.5	A
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	°C/W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

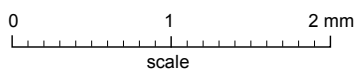
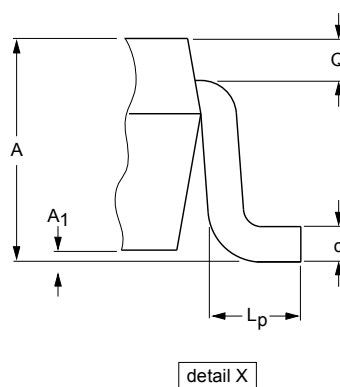
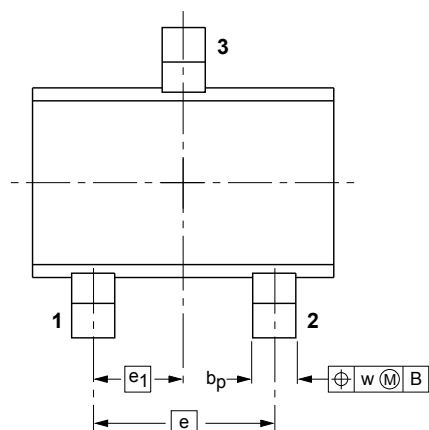
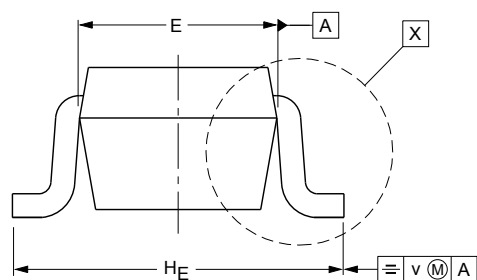
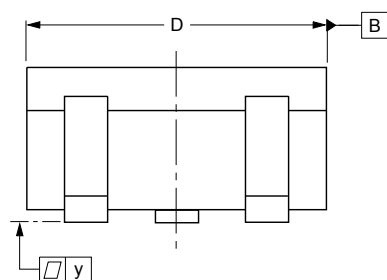
■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-0.1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-100	nA
Collector cut-off current	I_{CEO}	$V_{CE}=-20V, I_B=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	120		400	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$			-1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$			-1	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA, f=30MHz$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			20	pF

RANK	SS8550W
RANGE	200 - 350
MARKING	Y2



■ SOT-323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2